

ABSTRACT

Provided are a reflective mask for EUV lithography which can form a transfer pattern with high dimension accuracy with respect to fine line-like patterns, and a reflective mask blank that is used for the reflective mask. A reflective mask blank 10 for EUV lithography in which a multi-layer reflection film 2 that reflects EUV light and an absorption layer 3 that absorbs EUV light are laminated on a substrate 1 in the stated order from the substrate 1 side, wherein the absorption layer 3 has a refractive index of 0.930 or less and an extinction coefficient of 0.025 or more for EUV light having a wavelength of 13.5 nm, and a phase difference between reflected light from a surface of the multi-layer reflection film and reflected light from a surface of the absorption layer with respect to an incident ray of the EUV light having a wavelength of 13.5 nm is 220 to 280°, and a reflective mask in which a mask pattern is formed on the absorption layer 3.